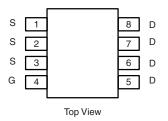


Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
	0.00875 at V _{GS} = - 4.5 V	- 14			
- 20	0.01075 at V _{GS} = - 2.5 V	- 12			
	0.0135 at V _{GS} = - 1.8 V	- 11			





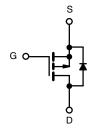
FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFET

APPLICATIONS

Game Station
Load Switch





P-Channel MOSFET

Ordering Information: Si4421DY-T1-E3 (Lead (Pb)-free) Si4421DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 14	- 10		
Continuous Drain Current $(T_j = 150^{\circ} C)$	T _A = 70 °C		- 11.5	- 8	А	
Pulsed Drain Current		I _{DM}	- 40		~	
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 2.7	- 1.36		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.0	1.5	W	
	T _A = 70 °C		1.9	0.95	vv	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mauinauna lunation ta Anakianta	t ≤ 10 s	R _{thJA}	33	42	
Maximum Junction-to-Ambient ^a	Steady State		70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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Parameter	Symbol	Test Conditions M		Тур.	Max.	Unit	
Static				•	•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -850 \ \mu A$	- 0.4		- 0.8	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
	I _{DSS}	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	μA	
Zero Gate Voltage Drain Current		V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 70 °C	/, T _J = 70 °C		- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -4.5 V$	- 30			А	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 14 A		0.007	0.00875		
	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -12 \text{ A}$		0.0085	0.01075	Ω	
		V _{GS} = - 1.8 V, I _D = - 11 A		0.011	0.0135		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 14 A		55		S	
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S}$ = - 2.7 A, $V_{\rm GS}$ = 0 V		- 0.6	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Qg			82	125		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 14 A		10		nC	
Gate-Drain Charge	Q _{gd}			27		1	
Gate Resistance	Rg			3		Ω	
Turn-On Delay Time	t _{d(on)}			45	70		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		90	140		
Turn-Off Delay Time t _{d(off)}		$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		350	550	ns	
Fall Time	t _f			170	260		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/μs		135	210		

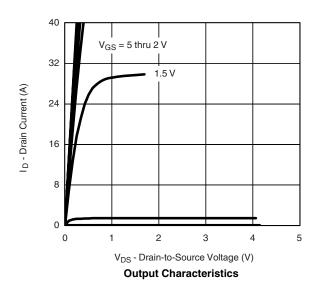
Notes:

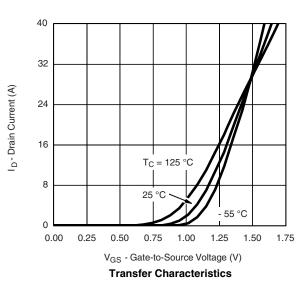
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



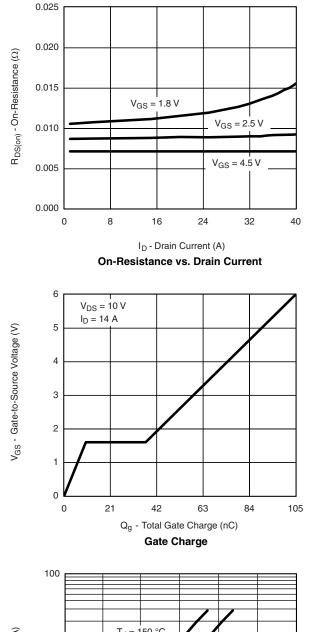


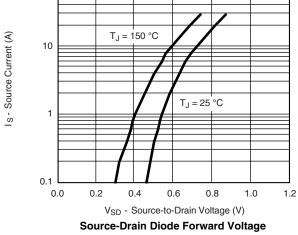
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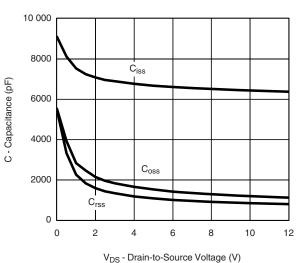
Si4421DY Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

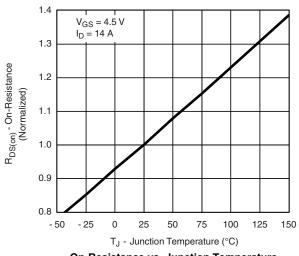
VISHAY



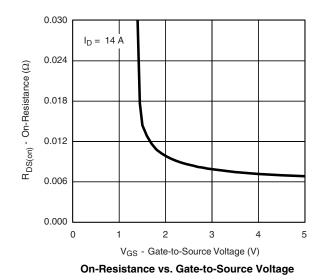




Capacitance



On-Resistance vs. Junction Temperature



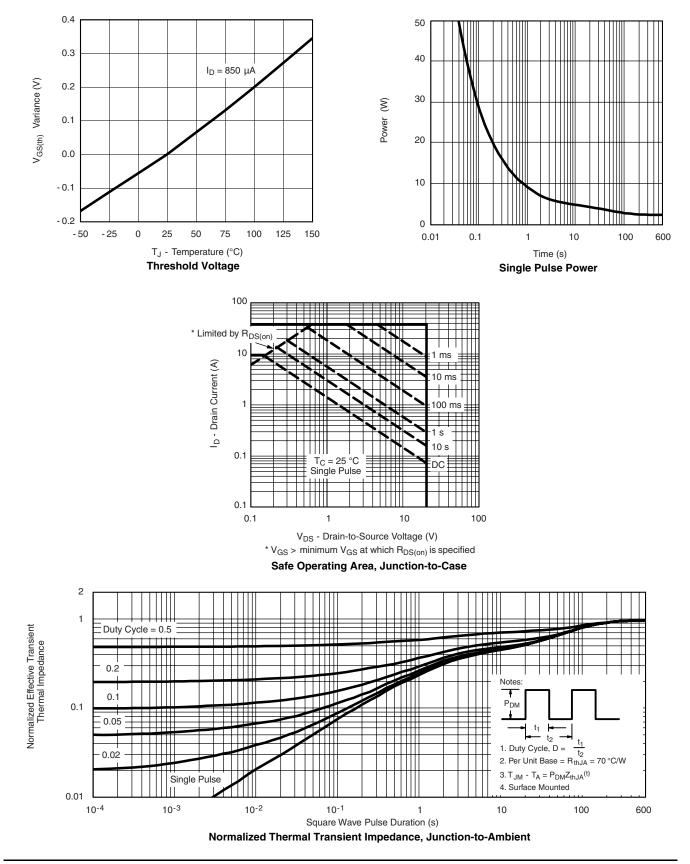
Document Number: 72114 S-82282-Rev. C, 22-Sep-08

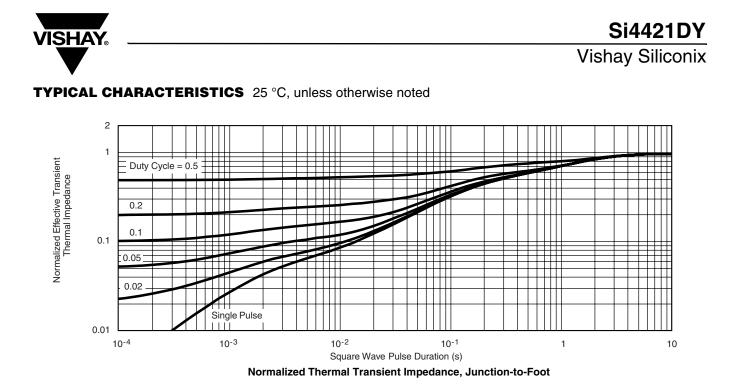
Si4421DY





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





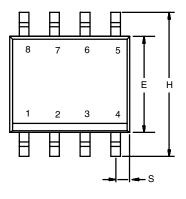
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72114.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





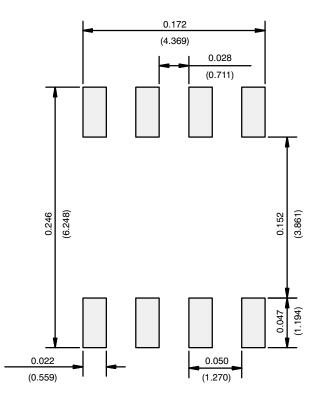
	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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